





TPS65100 TPS65105

SLVS496B-SEPTEMBER 2003-REVISED MARCH 2004

### TRIPLE OUTPUT LCD SUPPLY WITH LINEAR REGULATOR AND VCOM BUFFER

### **FEATURES**

- 2.7-V to 5.8-V Input Voltage Range
- 1.6-MHz Fixed Switching Frequency
- 3 Independent Adjustable Outputs
- Main Output of up to 15 V With < 1% Output</li>
   Voltage Accuracy
- Negative Output Voltage Down to -12 V/20 mA
- Positive Output Voltage up to 30 V/20 mA
- Integrated VCOM Buffer
- Auxiliary 3.3-V Linear Regulator Controller
- Internal Soft Start
- Internal Power-On Sequencing
- Fault Detection of all Outputs
- Thermal Shutdown
- Available in TSSOP-24 and QFN-24 PowerPAD™ Packages

### **APPLICATIONS**

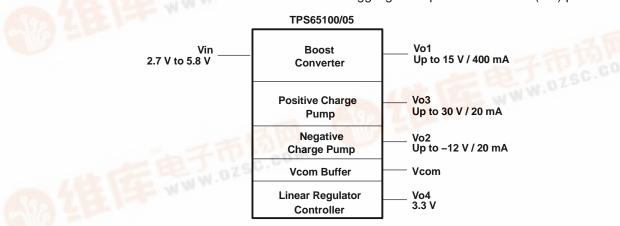
- TFT LCD Displays for Notebooks
- TFT LCD Displays for Monitors
- Portable DVD Players
- Tablet PCs
- Car Navigation Systems
- Industrial Displays

### **DESCRIPTION**

The TPS65100/05 offers a compact and small power supply solution that provides all three voltages required by thin film transistor (TFT) LCD displays. The auxiliary linear regulator controller can be used to generate a 3.3-V logic power rail for systems powered by a 5-V supply rail only.

The main output, Vo1, is a 1.6-MHz, fixed-frequency PWM boost converter providing the source drive voltage for the LCD display. The device is available in two versions with different internal switch current limits to allow the use of a smaller external inductor when lower output power is required. The TPS65100 has a typical switch current limit of 2.3 A, and the TPS65105 has a typical switch current limit of 1.37 A. integrated adjustable charge doubler/tripler provides the positive LCD gate drive voltage. An externally adjustable negative charge pump provides the negative gate drive voltage. Due to the high 1.6-MHz switching frequency of the charge pumps, inexpensive and small 220-nF capacitors can be used.

The TPS65100/05 has an integrated VCOM buffer to power the LCD backplane. For LCD panels powered by 5 V only, the TPS65100/05 has a linear regulator controller using an external transistor to provide a regulated 3.3-V output for the digital circuits. For maximum safety, the entire device goes into shutdown as soon as one of the outputs is out of regulation. The device can be enabled again by toggling the input or the enable (EN) pin to GND.



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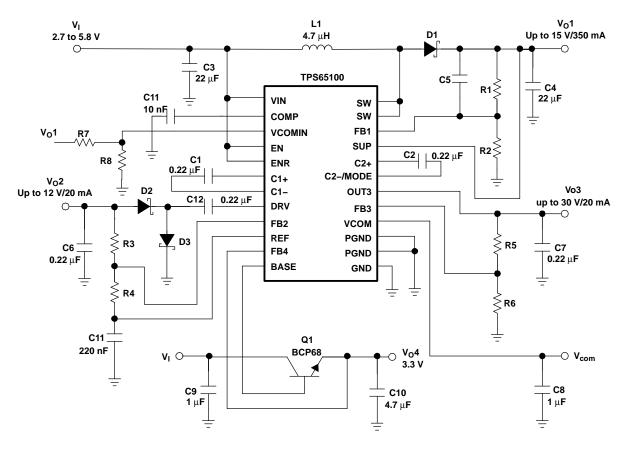
PowerPAD is a trademark of Texas Instruments.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### **TYPICAL APPLICATION CIRCUIT**



### **ORDERING INFORMATION**

| _        | T LINEAR REGULATOR MINIMUM SWITCH |               | PACK        | PACKAGE <sup>(1)</sup> |          |  |
|----------|-----------------------------------|---------------|-------------|------------------------|----------|--|
| 'A       | OUTPUT VOLTAGE                    | CURRENT LIMIT | TSSOP       | QFN                    | MARKING  |  |
| -40°C to | 3.3 V                             | 1.6 A         | TPS65100PWP | TPS65100RGE            | TPS65100 |  |
| 85°C     | 3.3 V                             | 0.96 A        | TPS65105PWP | TPS65105RGE            | TPS65105 |  |

<sup>(1)</sup> The PWP and RGE packages are available taped and reeled. Add an R suffix to the device type (TPS65100PWPR) to order the device taped and reeled. The PWPR package has quantities of 2000 devices per reel, and the RGER package has 3000 devices per reel. Without suffix the PWP package only, is shipped in tubes with 60 devices per tube.



### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range (unless otherwise noted)(1)

|  | UNIT                             |
|--|----------------------------------|
| Voltages on pin VIN <sup>(2)</sup>           | -0.3 V to 6.0 V                  |
| Voltages on pin Vo1, SUP, PG (2)             | -0.3 V to 15.5 V                 |
| Voltages on pin EN, MODE, ENR <sup>(2)</sup> | -0.3 V to V <sub>I</sub> + 0.3 V |
| Voltage on VCOMIN                            | 14 V                             |
| Voltage on pin SW <sup>(2)</sup>             | 20 V                             |
| Continuous power dissipation                 | See Dissipation Rating Table     |
| Operating junction temperature range         | -40°C to 150°C                   |
| Storage temperature range                    | -65°C to 150°C                   |
| Lead temperature (soldering, 10 sec)         | 260°C                            |

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### **DISSIPATION RATINGS**

| PACKAGE      | R⊖ <sub>JA</sub>          | T <sub>A</sub> ≤25°C<br>POWER RATING | T <sub>A</sub> = 70°C<br>POWER RATING | T <sub>A</sub> = 85°C<br>POWER RATING |
|--------------|---------------------------|--------------------------------------|---------------------------------------|---------------------------------------|
| 24-Pin TSSOP | 30.13 C°/W (PWP soldered) | 3.3 W                                | 1.83 W                                | 1.32 W                                |
| 24-Pin QFN   | 30.0 C°/W                 | 3.3 W                                | 1.8 W                                 | 1.3 W                                 |

### RECOMMENDED OPERATING CONDITIONS

|                |                                | MIN | TYP | MAX | UNIT |
|----------------|--------------------------------|-----|-----|-----|------|
| VIN            | Input voltage range            | 2.7 |     | 5.8 | ٧    |
| L              | Inductor <sup>(1)</sup>        |     | 4.7 |     | μΗ   |
| T <sub>A</sub> | Operating free-air temperature | -40 |     | 85  | °C   |
| TJ             | Operating junction temperature | -40 |     | 125 | °C   |

<sup>(1)</sup> Refer to the application section for further information.

### **ELECTRICAL CHARACTERISTICS**

 $V_{in}$  = 3.3 V, EN = VIN, Vo1 = 10 V,  $T_A$  = -40°C to 85°C, typical values are at  $T_A$  = 25°C (unless otherwise noted)

|                      | PARAMETER                                      | TEST CONDITIONS  | MIN | TYP | MAX  | UNIT |
|----------------------|--|--|-----|-----|------|------|
| SUPPLY (             | CURRENT  |  |     |     | •    |      |
| V <sub>in</sub>      | Input voltage range                            |  | 2.7 |     | 5.8  | V    |
| I <sub>QIN</sub>     | Quiescent current into VIN                     | ENR = VCOMIN = GND, Vo3 = 2 ×Vo1,<br>Boost converter not switching |     | 0.7 | 0.9  | mA   |
|                      | Charge pump quiescent cur-                     | Vo1 = SUP = 10 V, Vo3 = 2 × Vo1                                    |     | 1.7 | 2.7  | A    |
| I <sub>QCharge</sub> | rent into SUP                                  | Vo1 = SUP = 10 V, Vo3 = 3× Vo1                                     |     | 3.9 | 6    | mA   |
| I <sub>QVCOM</sub>   | VCOM quiescent current into SUP                | ENR = GND, Vo1 = SUP = 10 V  |     | 750 | 1300 | μΑ   |
| I <sub>QEN</sub>     | LDO controller quiescent cur-<br>rent into VIN | ENR = VIN, EN = GND  |     | 300 | 800  | μΑ   |
| I <sub>SD</sub>      | Shutdown current into VIN                      | EN = ENR = GND   |     | 1   | 10   | μΑ   |
| V <sub>UVLO</sub>    | Undervoltage lockout threshold                 | VIN falling  |     | 2.2 | 2.4  | V    |
|                      | Thermal shutdown                               | Temperature rising   |     | 160 |      | °C   |
| LOGIC SI             | GNALS EN, ENR                                  |  |     |     | •    |      |
| V <sub>IH</sub>      | High-level input voltage                       |  | 1.5 |     |      | V    |

<sup>(2)</sup> All voltage values are with respect to network ground terminal.



# **ELECTRICAL CHARACTERISTICS (continued)**

 $V_{in}$  = 3.3 V, EN = VIN, Vo1 = 10 V,  $T_A$  = -40°C to 85°C, typical values are at  $T_A$  = 25°C (unless otherwise noted)

|                                  | PARAMETER                                  | TEST CONDITIONS   | MIN   | TYP   | MAX   | UNIT |  |
|----------------------------------|--|---|-------|-------|-------|------|--|
| V <sub>IL</sub>                  | Low-level input voltage                    |   |       |       | 0.4   | V    |  |
| I <sub>Ileak</sub>               | Input leakage current                      | EN = GND or VIN   |       | 0.01  | 0.1   | μA   |  |
| MAIN BOO                         | OST CONVERTER                              |   | •     |       | •     |      |  |
| Vo1                              | Output voltage range                       |   | 5     |       | 15    | V    |  |
| V <sub>O1</sub> - V <sub>I</sub> | Minimum input to output voltage difference |   | 1     |       |       | V    |  |
| V <sub>REF</sub>                 | Reference voltage                          |   | 1.205 | 1.213 | 1.219 | V    |  |
| V <sub>FB</sub>                  | Feedback regulation voltage                |   | 1.136 | 1.146 | 1.154 | V    |  |
| I <sub>FB</sub>                  | Feedback input bias current                |   |       | 10    | 100   | nA   |  |
|                                  | N-MOSFET on-resistance                     | Vo1 = 10.0 V, I <sub>sw</sub> = 500 mA  |       | 195   | 290   |      |  |
| r <sub>DS(ON)</sub>              | (Q1)                                       | Vo1 = 5.0 V, I <sub>sw</sub> = 500 mA   |       | 285   | 420   | mΩ   |  |
|                                  | N-MOSFET switch current                    | TPS65100  | 1.6   | 2.3   | 2.6   | Α    |  |
| I <sub>LIM</sub>                 | limit (Q1)                                 | TPS65105  | 0.96  | 1.37  | 1.56  | Α    |  |
|                                  | P-MOSFET on-resistance                     | Vo1 = 10.0 V, I <sub>sw</sub> = 100 mA  |       | 9     | 15    |      |  |
| r <sub>DS(ON)</sub>              | (Q2)                                       | Vo1 = 5.0 V, I <sub>sw</sub> = 100 mA   |       | 14    | 22    | Ω    |  |
| I <sub>MAX</sub>                 | Maximum P-MOSFET peak switch current       |   |       |       | 1     | Α    |  |
| I <sub>leak</sub>                |  | V <sub>sw</sub> = 15 V  | '     | 1     | 10    | μA   |  |
|                                  | Switch leakage current                     | $V_{sw} = 0 \text{ V}$  |       | 1     | 10    |      |  |
| $f_{SW}$                         | 0 111 / (                                  | 0°C ≤ T <sub>A</sub> ≤ 85°C   | 1.295 | 1.6   | 2.1   | MHz  |  |
|                                  | Oscillator frequency                       | -40°C ≤ T <sub>A</sub> ≤ 85°C   | 1.191 | 1.6   | 2.1   |      |  |
|                                  | Line regulation                            | $2.7 \text{ V} \le \text{V}_{\text{I}} \le 5.7 \text{ V}, \text{ I}_{\text{load}} = 100 \text{ mA}$                 |       | 0.012 |       | %/V  |  |
|                                  | Load regulation                            | 0 mA ≤ I <sub>O</sub> ≤ 300 mA  |       | 0.2   |       | %/A  |  |
| NEGATIVI                         | E CHARGE PUMP Vo2                          |   | Į.    |       |       |      |  |
| Vo2                              | Output voltage range                       |   | -2    |       |       | V    |  |
| V <sub>ref</sub>                 | Reference voltage                          |   | 1.205 | 1.213 | 1.219 | V    |  |
| V <sub>FB</sub>                  | Feedback regulation voltage                |   | -36   | 0     | 36    | mV   |  |
| I <sub>FB</sub>                  | Feedback input bias current                |   |       | 10    | 100   | nA   |  |
| 10                               | Q8 P-Channel switch RDSon                  |   |       | 4.3   | 8     | Ω    |  |
| r <sub>DS(ON)</sub>              | Q9 N-Channel switch RDSon                  | I <sub>O</sub> = 20 mA  |       | 2.9   | 4.4   |      |  |
| I <sub>O</sub>                   | Minimum output current                     |   | 20    |       |       | mA   |  |
| -0                               | Line regulation                            | 7 V ≤ Vo1 ≤ 15 V, I <sub>load</sub> = 10 mA, Vo2 = -5.0 V   |       | 0.09  |       | %/V  |  |
|                                  | Load regulation                            | 1 mA $\leq$ I <sub>O</sub> $\leq$ 20 mA, Vo2 = -5.0 V   |       | 0.126 |       | %/mA |  |
| POSITIVE                         | CHARGE PUMP Vo3                            | 0 - 7   |       |       | 1     |      |  |
| Vo3                              | Output voltage range                       |   |       |       | 30    | V    |  |
| V <sub>ref</sub>                 | Reference voltage                          |   | 1.205 | 1.213 | 1.219 | V    |  |
| V <sub>FB</sub>                  | Feedback regulation voltage                |   | 1.187 | 1.214 | 1.238 | V    |  |
| I <sub>FB</sub>                  | Feedback input bias current                |   | 1.107 | 10    | 100   | nA   |  |
| ·rb                              | Q3 P-Channel switch RDSon                  |   |       | 9.9   | 15.5  | 11/1 |  |
|                                  | Q4 N-Channel switch RDSon                  |   |       | 1.1   | 1.8   |      |  |
| r <sub>DS(ON)</sub>              | Q5 P-Channel switch RDSon                  | I <sub>O</sub> = 20 mA  |       | 4.6   | 8.5   | Ω    |  |
|                                  | Q6 N-Channel switch RDSon                  |   |       | 1.2   | 2.2   |      |  |
|                                  | D1 – D4 Shottky diode for-                 |   |       | 610   |       | m\/  |  |
| V <sub>d</sub>                   | ward voltage                               | I <sub>D1-D4</sub> = 40 mA  |       | 010   | 720   | mV   |  |
| l <sub>o</sub>                   | Minimum output current                     |   | 20    |       |       | mA   |  |
|                                  | Line regulation                            | $10 \text{ V} \le \text{Vo1} \le 15 \text{ V}, \text{ I}_{\text{load}} = 10 \text{ mA}, \text{ Vo3} = 27 \text{ V}$ |       | 0.56  |       | %/V  |  |
|                                  | Load regulation                            | 1 mA $\leq$ I <sub>O</sub> $\leq$ 20 mA, Vo3 = 27 V   |       | 0.05  |       | %/mA |  |



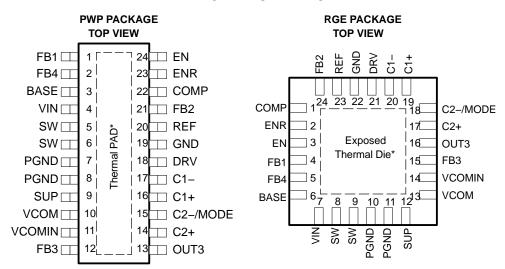
### **ELECTRICAL CHARACTERISTICS (continued)**

 $V_{in}$  = 3.3 V, EN = VIN, Vo1 = 10 V,  $T_A$  = -40°C to 85°C, typical values are at  $T_A$  = 25°C (unless otherwise noted)

|                        | PARAMETER                  | TEST CONDITIONS  | MIN  | TYP           | MAX     | UNIT |  |
|------------------------|----------------------------|--|------|---------------|---------|------|--|
| LINEAR                 | REGULATOR CONTROLLER Vo4   |  |      | ,             |         |      |  |
| Vo4                    | Output voltage             | $4.5 \text{ V} \le \text{V}_1 \le 5.5 \text{V}, \ 10 \text{ mA} \le \text{I}_0 \le 500 \text{ mA}$ | 3.2  | 3.3           | 3.4     | V    |  |
|                        | Marrian and Indian arrange | V <sub>I</sub> - Vo4 - V <sub>BE</sub> ≥ 0.5 V <sup>(1)</sup>                                      | 13.5 | 19            |         |      |  |
| I <sub>BASE</sub>      | Maximum base drive current | V <sub>I</sub> - Vo4 - V <sub>BE</sub> ≥ 0.75 V <sup>(1)</sup>                                     | 20   | 27            |         | mA   |  |
|                        | Line regulation            | 4.75 V ≤ V <sub>I</sub> ≤ 5.5 V, I <sub>load</sub> = 500 mA  |      | 0.186         |         | %/V  |  |
|                        | Load regulation            | 1 mA $\leq$ I <sub>O</sub> $\leq$ 500 mA, V <sub>I</sub> = 5.0 V                                   |      | 0.064         |         | %/A  |  |
|                        | Start up current           | Vo4 ≤ 0.8 V  | 11   | 20            | 25      | mA   |  |
| VCOM B                 | UFFER                      |  |      |               | •       |      |  |
| V <sub>cm</sub>        | Common mode input range    |  | 2.25 |               | (Vo1)-2 | V    |  |
| V <sub>os</sub>        | Input offset voltage       | $I_0 = 0 \text{ mA}$   | -25  |               | +25     | mV   |  |
|                        |                            | $I_0 = \pm 25 \text{ mA}$  | -30  |               | 37      |      |  |
|                        | DO Least remodelle         | $I_0 = \pm 50 \text{ mA}$  | -45  |               | 55      | mV   |  |
|                        | DC Load regulation         | $I_0 = \pm 100 \text{ mA}$   | -72  |               | 85      |      |  |
|                        |                            | $I_0 = \pm 150 \text{ mA}$   | -97  |               | 110     |      |  |
| I <sub>B</sub>         | VCOMIN Input bias current  |  | -300 | -30           | 300     | nA   |  |
|                        |                            | Vo1 = 15 V   | 1.2  |               |         | Α    |  |
| I <sub>peak</sub>      | Peak output current        | Vo1 = 10 V   | 0.65 |               |         | Α    |  |
|                        |                            | Vo1 = 5 V  | 0.15 |               |         | Α    |  |
| FAULT P                | PROTECTION THRESHOLDS      |  |      |               |         |      |  |
| V <sub>(th, VO1)</sub> |                            | Vo1 Rising   | -12  | -8.75%<br>Vo1 | -6      | V    |  |
| V <sub>(th, VO2)</sub> | Shutdown threshold         | Vo2 Rising   | -13  | -9% Vo2       | -5      | V    |  |
| V <sub>(th, VO3)</sub> |                            | Vo3 Rising   | -11  | -8% Vo3       | -5      | V    |  |

(1) With V<sub>in</sub> = supply voltage of the TPS65100/05, Vo4 = output voltage of the regulator, V<sub>BE</sub> = basis emitter voltage of external transistor

### **DEVICE INFORMATION**





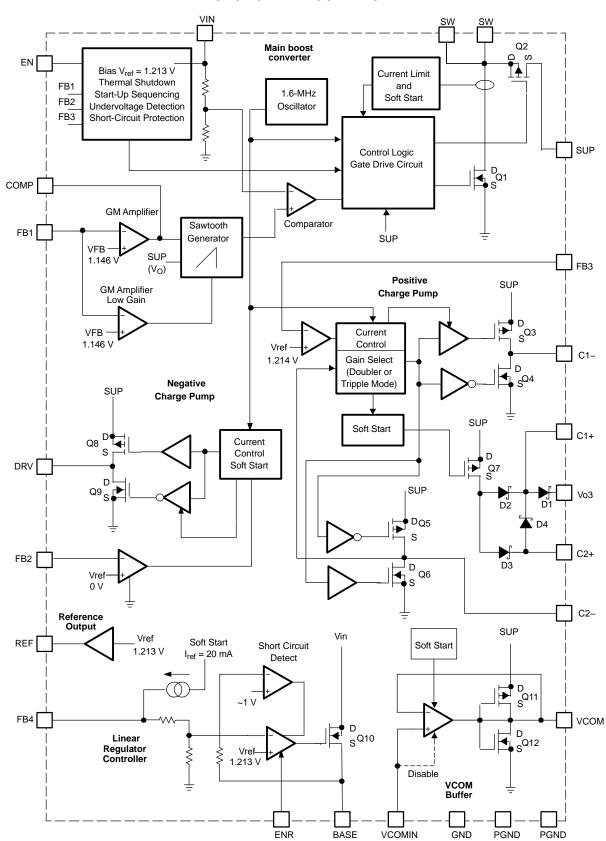
# **DEVICE INFORMATION (continued)**

### **Terminal Functions**

| TE                        | RMINAL       |              |     |  |
|---------------------------|--------------|--------------|-----|--|
| NAME                      | NO.<br>(PWP) | NO.<br>(RGE) | 1/0 | DESCRIPTION  |
| VIN                       | 4            | 7            | I   | Input voltage pin of the device  |
| EN                        | 24           | 3            | I   | Enable pin of the device. This pin should be terminated and not be left floating. A logic high enables the device and a logic low shuts down the device.   |
| COMP                      | 22           | 1            |     | Compensation pin for the main boost converter. A small capacitor is connected to this pin.   |
| VCOMIN                    | 11           | 14           | I   | Positive input terminal of the VCOM buffer. When the VCOM buffer is not used, this terminal can be connected to GND to reduce the overall quiescent current of the IC.   |
| ENR                       | 23           | 2            | I   | Enable pin of the linear regulator controller. This pin should be terminated and not be left floating. Logic high enables the regulator and a logic low puts the regulator in shutdown.  |
| C1+                       | 16           | 19           |     | Positive terminal of the charge pump flying capacitor  |
| C1-                       | 17           | 20           |     | Negative terminal of the charge pump flying capacitor  |
| DRV                       | 18           | 21           | 0   | External charge pump driver  |
| FB2                       | 21           | 24           | - 1 | Feedback pin of negative charge pump   |
| REF                       | 20           | 23           | 0   | Internal reference output typically 1.23 V   |
| FB4                       | 2            | 5            | I   | Feedback pin of the linear regulator controller. The linear regulator controller is set to a fixed output voltage of 3.3 V or 3.0 V depending on the version.  |
| BASE                      | 3            | 6            | 0   | Base drive output for the external transistor  |
| GND                       | 19           | 22           |     | Ground   |
| PGND                      | 7, 8         | 10, 11       |     | Power ground   |
| VCOM                      | 10           | 13           | 0   | VCOM buffer output   |
| FB3                       | 12           | 15           | I   | Feedback pin of positive charge pump   |
| OUT3                      | 13           | 16           | 0   | Positive charge pump output  |
| C2-/MODE                  | 15           | 18           |     | Negative terminal of the charge pump flying capacitor and charge pump MODE pin. If the flying capacitor is connected to this pin, the converter operates in a voltage tripler mode. If the charge pump needs to operate in a voltage doubler mode, the flying capacitor is removed and the C2-/MODE pin should be connected to GND.            |
| C2+                       | 14           | 17           |     | Positive terminal for the charge pump flying capacitor. If the device runs in voltage doubler mode, this pin should be left open.  |
| SUP                       | 9            | 12           | I   | Supply pin of the positive, negative charge pump, boost converter gate drive circuit, and VCOM buffer. This pin should be connected to the output of the main boost converter and cannot be connected to any other voltage source. For performance reasons, it is not recommended for a bypass capacitor to be connected directly to this pin. |
| FB1                       | 1            | 4            | 1   | Feedback pin of the boost converter  |
| SW                        | 5, 6         | 8, 9         | I   | Switch pin of the boost converter  |
| PowerPAD™/<br>Thermal Die |              |              |     | The PowerPad or exposed thermal die needs to be connected to the power ground pins (PGND)  |



### **FUNCTIONAL BLOCK DIAGRAM**

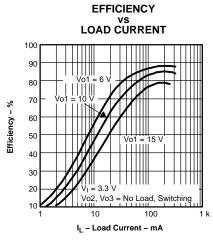


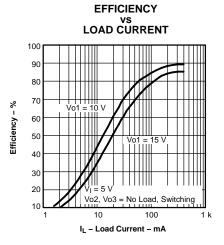


### **TYPICAL CHARACTERISTICS**

# **Table of Graphs**

|                     |   |                                      | FIGURE |
|---------------------|---|--------------------------------------|--------|
| Main Bo             | ost Converter                                       |                                      | -      |
|                     | Efficiency, main boost converter Vo1                | vs Load current                      | 1      |
| η                   | Efficiency, main boost converter Vo1                | vs Load current                      | 2      |
|                     | Efficiency  | vs Input voltage                     | 3      |
| f <sub>sw</sub>     | Switching frequency                                 | vs Free-air temperature              | 4      |
| r <sub>DS(on)</sub> | r <sub>DS(on)</sub> N-Channel main switch Q1        | vs Free-air temperature              | 5      |
|                     | PWM operation, continuous mode                      |                                      | 6      |
|                     | PWM operation at light load                         |                                      | 7      |
|                     | Load transient response, C <sub>out</sub> = 22 μF   |                                      | 8      |
|                     | Load transient response, C <sub>out</sub> = 2*22 μF |                                      | 9      |
|                     | Power-up sequencing                                 |                                      | 10     |
|                     | Soft start Vo1                                      |                                      | 11     |
| Negative            | Charge Pump   | ·                                    |        |
| I <sub>max</sub>    | Vo2 Maximum load current                            | vs Output voltage Vo1                | 12     |
| Positive            | Charge Pump   |                                      | -      |
| I <sub>max</sub>    | Vo3 Maximum load current                            | vs Output voltage Vo1 (doubler mode) | 13     |
| I <sub>max</sub>    | Vo3 Maximum load current                            | vs Output voltage Vo1 (tripler mode) | 14     |





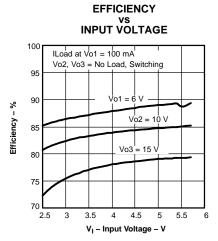


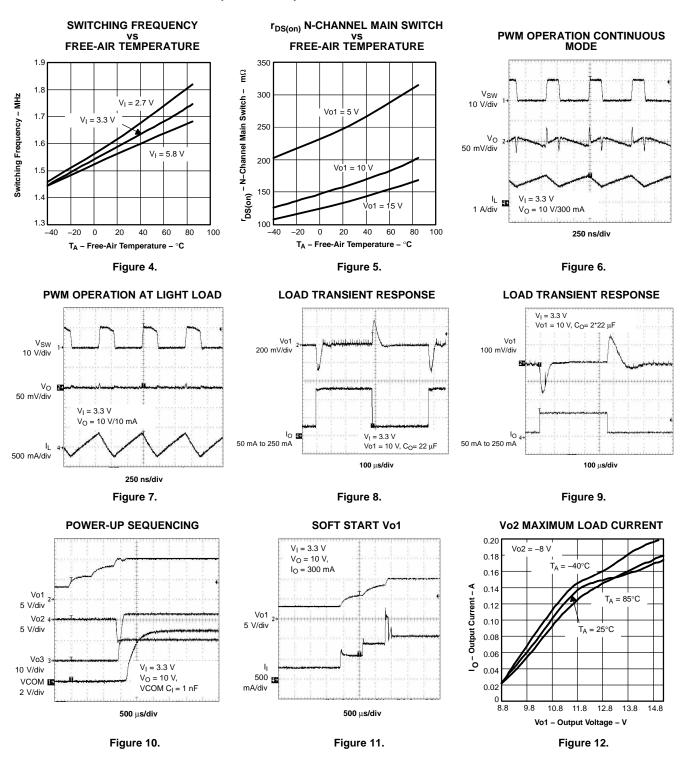
Figure 1.

Figure 2.

Figure 3.

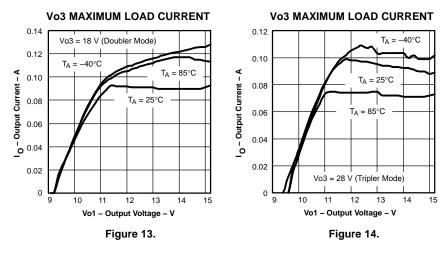


### **TYPICAL CHARACTERISTICS (continued)**





### TYPICAL CHARACTERISTICS (continued)



#### **DETAILED DESCRIPTION**

The TPS65100/05 consists of a main boost converter operating with a fixed switching frequency of 1.6 MHz to allow for small external components. The boost converter output voltage Vo1 is also the input voltage, connected via the pin SUP, for the positive and negative charge pumps and the bias supply for the VCOM buffer. The linear regulator controller is independent from this system with its own enable pin. This allows the linear regulator controller to continue to operate while the other supply rails are disabled or in shutdown due to a fault condition on one of their outputs. See the functional block diagram for more information.

### **Main Boost Converter**

The main boost converter operates with PWM and a fixed switching frequency of 1.6 MHz. The converter uses a unique fast response, voltage mode controller scheme with input voltage feedforward. This achieves excellent line and load regulation (0.2% A load regulation typical) and allows the use of small external components. To add higher flexibility to the selection of external component values the device uses external loop compensation. Although the boost converter looks like a nonsynchronous boost converter topology operating in discontinuous mode at light load, the TPS65100/05 maintains continuous conduction even at light load currents.

This is achieved with a unique architecture using an external Schottky diode and an integrated MOSFET in parallel connected between SW and SUP (see the functional block diagram). The integrated MOSFET Q2 allows the inductor current to become negative at light load conditions. For this purpose, a small integrated P-channel MOSFET with typically 10  $\Omega$  r<sub>DSon</sub> is sufficient. When the inductor current is positive, the external Schottky diode with the lower forward voltage conducts the current. This causes the converter to operate with a fixed frequency in continuous conduction mode over the entire load current range. This avoids the ringing on the switch pin as seen with a standard nonsynchronous boost converter and allows a simpler compensation for the boost converter.

#### **VCOM Buffer**

VCOMIN is the input of the VCOM buffer. If the VCOM buffer is not required for certain applications, it is possible to shut down the VCOM buffer by statically connecting VCOMIN to ground, reducing the overall quiescent current. The VCOM buffer features soft start avoiding a large voltage drop at Vo1 during start-up. The VCOMIN cannot be pulled dynamically to ground during operation.

### **Enable and Power On Sequencing (EN, ENR)**

The device has two enable pins. These pins should be terminated and not left floating to prevent unpredictable operation. Pulling the enable pin (EN) high enables the device and starts the power on sequencing with the main boost converter Vo1 coming up first then the negative and positive charge pumps and the VCOM buffer. If the VCOMIN pin is held low, the VCOM buffer remains disabled. The linear regulator has an independent enable pin (ENR). Pulling this pin low disables the regulator, and pulling this pin high enables this regulator.



### **DETAILED DESCRIPTION (continued)**

If the enable pin EN is pulled high, the device starts its power on sequencing. The main boost converter starts up first with its soft start. If the output voltage has reached 91.25% of its output voltage, the negative charge pump comes up next. The negative charge pump starts with a soft start and when the output voltage has reached 91% of the nominal value, the positive charge pump comes up with a soft start. The VCOM buffer is enabled as soon as the positive charge pump has reached its nominal value and VCOMIN is greater than typically 1.0 V.

Pulling the enable pin low shuts down the device. Depended on load current and output capacitance, each of the outputs goes down.

### **Positive Charge Pump**

The TPS65100/05 has a fully regulated integrated positive charge pump generating Vo3. The input voltage for the charge pump is applied to the SUP pin that is equal to the output of the main boost converter Vo1. The charge pump is capable of supplying a minimum load current of 20 mA. Depending on the voltage difference between Vo1 and Vo3 higher load currents are possible. See Figure 13 and Figure 14.

### **Negative Charge Pump**

The TPS65100/05 has a regulated negative charge pump using two external Schottky diodes. The input voltage for the charge pump is applied to the SUP pin that is connected to the output of the main boost converter Vo1. The charge pump inverts the main boost converter output voltage and is capable of supplying a minimum load current of 20 mA. Depending on the voltage difference between Vo1 and Vo2, higher load currents are possible. See Figure 12.

### **Linear Regulator Controller**

The TPS65100/05 includes a linear regulator controller to generate a 3.3-V rail which is useful when the system is powered from a 5-V supply. The regulator is independent from the other voltage rails of the device and has its own enable (ENR).

#### Soft Start

The main boost converter as well as the charge pumps, linear regulator, and VCOM buffer have an internal soft start. This avoids heavy voltage drops at the input voltage rail or at the output of the main boost converter Vo1 during start-up caused by high inrush currents. See Figure 10 and Figure 11.

#### **Fault Protection**

All the outputs of the TPS65100/05 have short circuit detection and cause the device to go into shutdown. The main boost converter has overvoltage and undervoltage protection. If the output voltage Vo1 rises above the overvoltage protection threshold of typically 5% of Vo1, then the device stops switching but remains operational. When the output voltage falls below this threshold again, then the converter continues operation. When the output voltage falls below the undervoltage protection threshold of typically 8.75% of Vo1, in case of a short circuit condition, then the TPS65100/05 goes into shutdown. Because there is a direct pass from the input to the output through the diode, the short circuit condition remains. If this condition needs to be avoided, a fuse at the input or an output disconnect using a single transistor and resistor is required. The negative and positive charge pumps have an undervoltage lockout to protect the LCD panel of possible latch-up conditions in case of a short circuit condition or faulty operation. When the negative output voltage is typically above 9.5% of its output voltage (closer to ground), then the device enters shutdown. When the positive charge pump output voltage Vo3 is below 8% typ of its output voltage, then the device goes into shutdown as well. See the electrical characteristics table under fault protection thresholds. The device can be enabled again by toggling the enable pin (EN) below 0.4 V or by cycling the input voltage below the UVLO of 1.7 V. The linear regulator reduces the output current to typical 20 mA under a short circuit condition when the output voltage is typically < 1 V. See the functional block diagram. The linear regulator does not go into shutdown under a short-circuit condition.

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### **DETAILED DESCRIPTION (continued)**

### **Thermal Shutdown**

A thermal shutdown is implemented to prevent damage due to excessive heat and power dissipation. Typically, the thermal shutdown threshold is  $160^{\circ}$ C. If this temperature is reached, the device goes into shutdown. The device can be enabled by toggling the enable pin to low and back to high or by cycling the input voltage to GND and back to  $V_{I}$  again.



#### APPLICATION INFORMATION

#### **BOOST CONVERTER DESIGN PROCEDURE**

The first step in the design procedure is to calculate the maximum possible output current of the main boost converter under certain input and output voltage conditions. The following example is for a 3.3-V to 10-V conversion:

 $V_{in} = 3.3 \text{ V}$ ,  $V_{out} = 10 \text{ V}$ , Switch voltage drop  $V_{sw} = 0.5 \text{ V}$ , Schottky diode forward voltage  $V_D = 0.8 \text{ V}$ 

1. Duty cycle:

$$D = \frac{V_{out} + V_{D} - V_{in}}{V_{out} + V_{D} - V_{sw}} = \frac{10 \text{ V} + 0.8 \text{ V} - 3.3 \text{ V}}{10 \text{ V} + 0.8 \text{ V} - 0.5 \text{ V}} = 0.73$$

2. Average inductor current:

$$I_L = \frac{I_{out}}{1 - D} = \frac{300 \text{ mA}}{1 - 0.73} = 1.11 \text{ A}$$

3. Inductor peak-to-peak ripple current

$$\Delta i_L = \frac{\left[V_{in} - V_{SW}\right] \times D}{f_S \times L} = \frac{\left(3.3 \text{ V} - 0.5 \text{ V}\right) \times 0.73}{1.6 \text{ MHz} \times 4.2 \text{ }\mu\text{H}} = 304 \text{ mA}$$

4. Peak switch current:

$$I_{\text{swpeak}} = I_{\text{L}} + \frac{\Delta i_{\text{L}}}{2} = 1.11 \text{ A} + \frac{304 \text{ mA}}{2} = 1.26 \text{ A}$$

. The integrated switch, the inductor, and the external Schottky diode must be able to handle the peak switch current. The calculated peak switch current has to be equal to or lower than the minimum N-MOSFET switch current limit as specified in the electrical characteristics table (1.6 A for the TPS65100 and 0.96 A for the TPS65105). If the peak switch current is higher, then the converter cannot support the required load current. This calculation must be done for the minimum input voltage where the peak switch current is highest. The calculation includes conduction losses like switch  $r_{\rm DSon}$  (0.5 V) and diode forward drop voltage losses (0.8 V). Additional switching losses, inductor core and winding losses, etc., require a slightly higher peak switch current in the actual application. The above calculation still allows a for good design and component selection.

#### **Inductor Selection**

Several inductors work with the TPS65100/05. Especially with the external compensation, the performance can be adjusted to the specific application requirements. The main parameter for inductor selection is the saturation current of the inductor which should be higher than the peak switch current as calculated above with additional margin to cover for heavy load transients and extreme start-up conditions. Another method is to choose the inductor with a saturation current at least as high as the minimum switch current limit of 1.6 A for the TPS65100 and 0.96 A for the TPS65105. The different switch current limits allow selection of a physically smaller inductor when less output current is required. The second important parameter is inductor dc resistance. Usually, the lower the dc resistance, the higher the efficiency. However, inductor dc resistance, is not the only parameter determining the efficiency. Especially for a boost converter where the inductor is the energy storage elemen,t the type and material of the inductor influences the efficiency as well. Especially at the high switching frequency of 1.6 MHz, inductor core losses, proximity effects, and skin effects become more important. Usually, an inductor with a larger form factor yields higher efficiency. The efficiency difference between different inductors can vary between 2% to 10%. For the TPS65100/05, inductor values between 3.3 µH and 6.8 µH are a good choice but other values can be used as well. Possible inductors are shown in Table 1.



### **APPLICATION INFORMATION (continued)**

**Table 1. Inductor Selection** 

| DEVICE    | INDUCTOR VALUE | COMPONENT SUPPLIER          | DIMENSIONS   | ISAT/DCR     |
|-----------|----------------|-----------------------------|--------------|--------------|
|           | 4.7 µH         | Coilcraft DO1813P-472HC     | 8.89*6.1*5.0 | 2.6 A/54 mΩ  |
|           | 4.2 µH         | Sumida CDRH5D28 4R2         | 5.7*5.7*3    | 2.2 A/23 mΩ  |
| TPS65100  | 4.7 µH         | Sumida CDC5D23 4R7          | 6*6*2.5      | 1.6 A/48 mΩ  |
| 117505100 | 3.3 µH         | Wuerth Elektronik 744042003 | 4.8*4.8*2.0  | 1.8 A/65 mΩ  |
|           | 4.2 µH         | Sumida CDRH6D12 4R2         | 6.5*6.5*1.5  | 1.8 A/60 mΩ  |
|           | 3.3 µH         | Sumida CDRH6D12 3R3         | 6.5*6.5*1.5  | 1.9 A/50 mΩ  |
|           | 3.3 µH         | Sumida CDPH4D19 3R3         | 5.1*5.1*2.0  | 1.5 A/26 mΩ  |
|           | 3.3 µH         | Coilcraft DO1606T-332       | 6.5*5.2*2.0  | 1.4 A/120 mΩ |
| TPS65105  | 3.3 µH         | Sumida CDRH2D18/HP 3R3      | 3.2*3.2*2.0  | 1.45 A/69 mΩ |
|           | 4.7 µH         | Wuerth Elektronik 744010004 | 5.5*3.5*1.0  | 1.0 A/260 mΩ |
|           | 3.3 µH         | Coilcraft LPO6610-332M      | 6.6*5.5*1.0  | 1.3 A/160 mΩ |

### **Output Capacitor Selection**

For the best output voltage filtering, a low ESR output capacitor is recommended. Ceramic capacitors have a low ESR value, but depending on the application, tantalum capacitors can be used as well. A 22-µF ceramic output capacitor works for most of the applications. Higher capacitor values can be used to improve the load transient regulation. See Table 2 for selection of the output capacitor. The output voltage ripple can be calculated as:

$$\Delta V_{out} = \frac{I_{out}}{C_{out}} \times \left[ \frac{1}{f_s} - \frac{I_p \times L}{V_{out} + V_d - V_{in}} \right] + I_p \times ESR$$

with:

I<sub>D</sub> = Peak current as described in the previous section peak current control

L = Selected inductor value

I<sub>out</sub> = Nominal load current

f<sub>s</sub> = Switching frequency

V<sub>d</sub> = Rectifier diode forward voltage (typically 0.3 V)

Cout = Selected output capacitor

ESR = Output capacitor ESR value

### **Input Capacitor Selection**

For good input voltage filtering, low ESR ceramic capacitors are recommended. A 22-µF ceramic input capacitor is sufficient for most of the applications. For better input voltage filtering, this value can be increased. See Table 2 and the typical applications for input capacitor recommendations.

**Table 2. Input and Output Capacitors Selection** 

| CAPACITOR  | VOLTAGE RATING | COMPONENT SUPPLIER        | COMMENTS         |
|------------|----------------|---------------------------|------------------|
| 22 μF/1210 | 16 V           | Taiyo Yuden EMK325BY226MM | C <sub>out</sub> |
| 22 μF/1206 | 6.3 V          | Taiyo Yuden JMK316BJ226   | C <sub>in</sub>  |

### **Rectifier Diode Selection**

To achieve high efficiency, a Schottky diode should be used. The voltage rating should be higher than the maximum output voltage of the converter. The average forward current should be equal to the average inductor current of the converter. The main parameter influencing the efficiency of the converter is the forward voltage and the reverse leakage current of the diode; both should be as low as possible. Possible diodes are: On Semiconductor MBRM120L, Microsemi UPS120E, and Fairchild Semiconductor MBRS130L.



### **Converter Loop Design and Stability**

The TPS65100/05 converter loop can be externally compensated and allows access to the internal transconductance error amplifier output at the COMP pin. A small feedforward capacitor across the upper feedback resistor divider speeds up the circuit as well. To test the converter stability and load transient performance of the converter, a load step from 50 mA to 250 mA is applied, and the output voltage of the converter is monitored. Applying load steps to the converter output is a good tool to judge the stability of such a boost converter.

### **Design Procedure Quick Steps**

- 1. Select the feedback resistor divider to set the output voltage.
- 2. Select the feedforward capacitor to place a zero at 50 kHz.
- 3. Select the compensation capacitor on pin COMP. The smaller the value, the higher the low frequency gain.
- 4. Use a  $50\text{-}k\Omega$  potentiometer in series to  $C_c$  and monitor  $V_{out}$  during load transients. Fine tune the load transient by adjusting the potentiometer. Select a resistor value that comes closest to the potentiometer resistor value. This needs to be done at the highest  $V_{in}$  and highest load current since the stability is most critical at these conditions.

#### Setting the Output Voltage and Selecting the Feedforward Capacitor

The output voltage is set by the external resistor divider and is calculated as:

$$V_{out} = 1.146 \text{ V} \times \left[ 1 + \frac{R1}{R2} \right]$$

Across the upper resistor a bypass capacitor is required to speed up the circuit during load transients as shown in Figure 15.

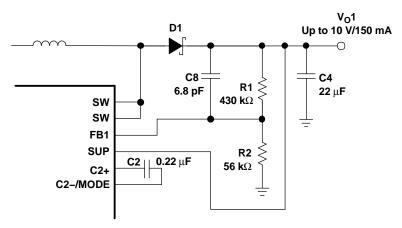


Figure 15. Feedforward Capacitor

Together with R1 the bypass capacitor C8 sets a zero in the control loop at approximately 50 kHz:

$$f_{Z} = \frac{1}{2 \times \pi \times C8 \times R1}$$

A value closest to the calculated value should be used. Larger feedforward capacitor values reduce the load regulation of the converter and cause load steps as shown in Figure 16.



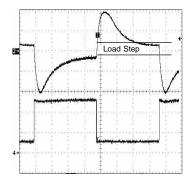


Figure 16. Load Step Caused By A Too Large Feedforward Capacitor Value

### Compensation

The regulator loop can be compensated by adjusting the external components connected to the COMP pin. The COMP pin is connected to the output of the internal transconductance error amplifier. A typical compensation scheme is shown in Figure 17.

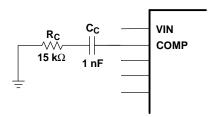


Figure 17. Compensation Network

The compensation capacitor  $C_c$  adjusts the low frequency gain and the resistor value adjusts the high frequency gain. The formula below calculates at what frequency the resistor increases the high frequency gain.

$$f_Z = \frac{1}{2 \times \pi \times Cc \times Rc}$$

Lower input voltages require a higher gain and therefore a lower compensation capacitor value. A good start is  $C_c = 1$  nF for a 3.3-V input and  $C_c = 2.2$  nF for a 5-V input. If the device operates over the entire input voltage range from 2.7 V to 5.8 V, a large compensation capacitor up to 10 nF is recommended. Figure 18 shows the load transient with a larger compensation capacitor, and Figure 19 shows a smaller compensation capacitor.

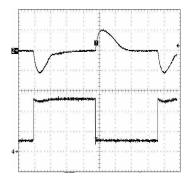


Figure 18.  $C_c = 4.7 \text{ nF}$ 



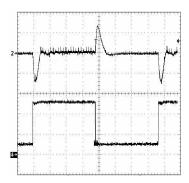


Figure 19.  $C_c = 1 \text{ nF}$ 

Lastly,  $R_c$  needs to be selected. A good practice is to use a 50-k $\Omega$  potentiometer and adjust the potentiometer for best load transient where no oscillations should occur. These tests have to be done at the highest  $V_{in}$  and highest load current because converter stability is most critical under these conditions. Figure 20, Figure 21, and Figure 22 show the fine tuning of the loop with  $R_c$ .

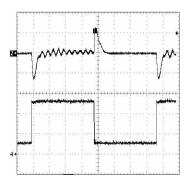


Figure 20. Overcompensated (Damped Oscillation),  $R_{\text{c}}$  Is Too Large

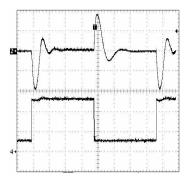


Figure 21. Undercompensated (Loop Is Too Slow),  $R_{\rm c}$  Is Too Small



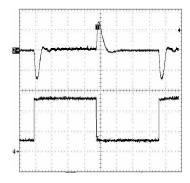


Figure 22. Optimum, Rc Is Ideal

### **Negative Charge Pump**

The negative charge pump provides a regulated output voltage by inverting the main output voltage Vo1. The negative charge pump output voltage is set with external feedback resistors.

The maximum load current of the negative charge pump depends on the voltage drop across the external Schottky diodes, the internal on resistance of the charge pump MOSFETS Q8 and Q9, and the impedance of the flying capacitor C12. When the voltage drop across these components is larger than the voltage difference from Vo1 to Vo2, the charge pump is in dropout, providing the maximum possible output current. Therefore, the higher the voltage difference between Vo1 and Vo2, the higher the possible load current. See Figure 12 for the possible output current versus boost converter voltage Vo1.

$$Vout_{min} = \text{-}(Vo1 - 2 \ V_D - Io \ (2 \times r_{DS(on)Q8} + 2 \times r_{DS(on)Q9} + X_{cfly}))$$

Setting the output voltage:

$$V_{out} = -V_{REF} \times \left[ 1 + \frac{R3}{R4} \right] + V_{REF} = -1.213 \text{ V} \times \left[ 1 + \frac{R3}{R4} \right] + 1.213 \text{ V}$$

$$R3 = R4 \times \left[ \frac{|V_{out}| + V_{REF}}{V_{REF}} - 1 \right] = R4 \times \left[ \frac{|V_{out}| + 1.213}{1.213} - 1 \right]$$

The lower feedback resistor value R4 should be in a range between 40 k $\Omega$  to 120 k $\Omega$  or the overall feedback resistance should be within 500 k $\Omega$  to 1 M $\Omega$ . Smaller values load the reference too heavily and larger values may cause stability problems. The negative charge pump requires two external Schottky diodes. The peak current rating of the Schottky diode has to be twice the load current of the output. For a 20-mA output current, the dual Schottky diode BAT54 or similar is a good choice.

### Positive Charge Pump

The positive charge pump can be operated in a voltage doubler mode or a voltage tripler mode depending on the configuration of the C2+ and C2-/MODE pins. Leaving the C2+ pin open and connecting C2-/MODE to GND forces the positive charge pump to operate in a voltage doubler mode. If higher output voltages are required, the positive charge pump can be operated as a voltage tripler. To operate the charge pump in the voltage tripler mode, a flying capacitor needs to be connected to C2+ and C2-/MODE.

The maximum load current of the positive charge pump depends on the voltage drop across the internal Schottky diodes, the internal on resistance of the charge pump MOSFETS, and the impedance of the flying capacitor. When the voltage drop across these components is larger than the voltage difference Vo1  $\times$  2 to Vo3 (doubler mode) or Vo1  $\times$  3 to Vo3 (tripler mode), then the charge pump is in dropout, providing the maximum possible output current. Therefore, the higher the voltage difference between Vo1  $\times$  2 (doubler) or Vo1  $\times$  3 (tripler) to Vo3, the higher the possible load current. See Figure 13 and Figure 14 for the output current versus boost converter voltage Vo1 and the following calculations.

Voltage doubler:

$$Vo3_{max} = 2 \times Vo1 - (2 V_D + 2 \times Io \times (2 \times r_{DS(on)Q5} + r_{DS(on)Q3} + r_{DS(on)Q4} + X_{C1}))$$



Voltage tripler:

$$Vo3_{max} = 3 \times Vo1 - (3 \times V_D + 2 \times Io \times (3 \times r_{DS(on)Q5} + r_{DS(on)Q3} + r_{DS(on)Q4} + X_{C1} + X_{C2}))$$

The output voltage is set by the external resistor divider and is calculated as:

$$V_{out} = 1.214 \times \left[ 1 + \frac{R5}{R6} \right]$$

$$R5 = R6 \times \left[ \frac{V_{out}}{V_{FB}} - 1 \right] = R6 \times \left[ \frac{V_{out}}{1.214} - 1 \right]$$

#### **VCOM Buffer**

The VCOM buffer is typically used to drive the backplane of a TFT panel. The VCOM output voltage is typically set to half of the main output voltage Vo1 plus a small shift to implement the specific compensation voltage. The TFT video signal gets coupled through the TFT storage capacitor plus the LCD cell capacitance to the output of the VCOM buffer. Because of these, short current pulses in the positive and negative direction appear at the output of the VCOM buffer. To minimize the output voltage ripple caused by the current pulses, a transconductance amplifier having a current source output and an output capacitor is used. The output capacitor supports the high frequency part of the current pulses drawn from the LCD panel. The VCOM buffer only needs to handle the low frequency portion of the current pulses. A 1-µF ceramic output capacitor is sufficient for most of the applications. When using other output capacitor values it is important to keep in mind that the output capacitor is part of the VCOM buffer loop stabilization.

The VCOM buffer has an integrated soft start to avoid voltage drops on Vo1 during start-up. The soft start is implemented as such that the VCOMIN is held low until the VCOM buffer is fully biased and the common mode range is reached. Then the positive input is released and the VCOM buffer output slowly comes up. Usually a 1-nF capacitor on VCOMIN to GND is used to filter high frequency noise coupled in from Vo1. The size of this capacitor together with the upper feedback resistor value determines the start-up time. The larger the capacitor from VCOMIN to GND, the slower the soft start.

#### Linear Regulator Controller

The TPS65100/05 includes a linear regulator controller to generate a 3.3-V rail when the system is powered from a 5-V supply. Because an external npn transistor is required, the input voltage of the TPS65100/05 applied to VIN needs to be higher than the output voltage of the regulator. To provide a minimum base drive current of 13.5 mA, a minimum internal voltage drop of 500 mV from  $V_{in}$  to  $V_{base}$  is required. This can be translated into a minimum input voltage on VIN for a certain output voltage as the following calculation shows:

$$VIN_{min} = Vo4 + V_{BE} + 0.5 V$$

The base drive current together with the  $h_{FE}$  of the external transistor determines the possible output current. Using a standard npn transistor like the BCP68 allows an output current of 1 A and using the BCP54 allows a load current of 337 mA for an input voltage of 5 V. Other transistors can be used as well depending on the required output current, power dissipation, and PCB space. The device is stable with a 4.7- $\mu$ F ceramic output capacitor. Larger output capacitor values can be used to improve the load transient response when higher load currents are required.

### Layout Considerations

For all switching power supplies, the layout is an important step in the design, especially at high-peak currents and switching frequencies. If the layout is not carefully designed, the regulator might show stability and EMI problems. Therefore, the traces carrying high-switching currents should be routed first using wide and short traces. The input filter capacitor should be placed as close as possible to the input pin VIN of the IC. See the evaluation module (EVM) for a layout example.



#### Thermal Information

An influential component of thermal performance of a package is board design. To take full advantage of the heat dissipation abilities of the PowerPAD or QFN package with exposed thermal die, a board that acts similar to a heat sink and allows the use of an exposed (and solderable) deep downset pad should be used. For further information, see the Texas Instrumens application notes (SLMA002) *PowerPAD Thermally Enhanced Package*, and (SLMA004) *PowerPAD Made Easy*. For the QFN package, see the application report (SLUA271) *QFN/SON PCB Attachement*.

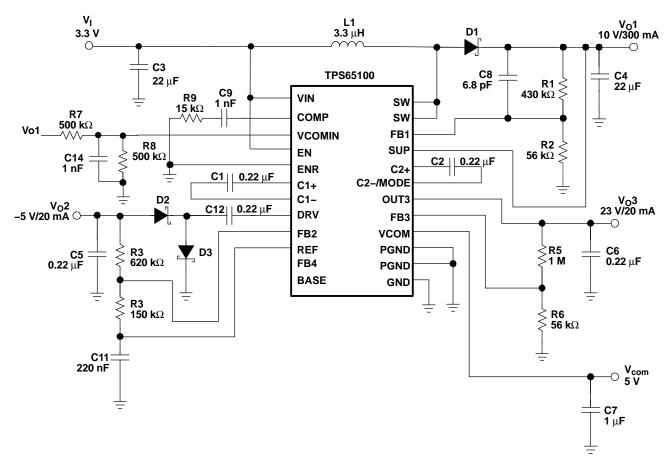


Figure 23. Typical Application, Notebook supply



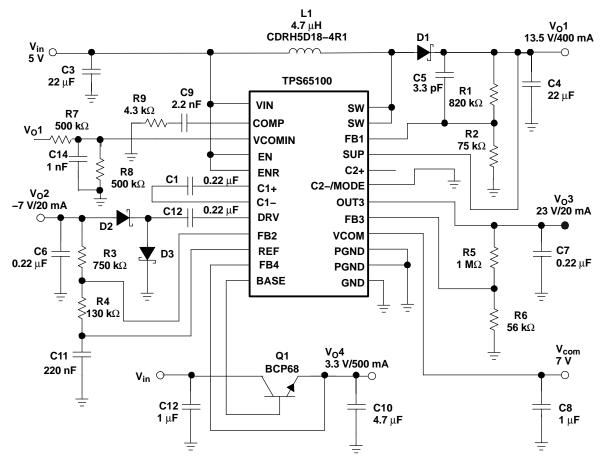
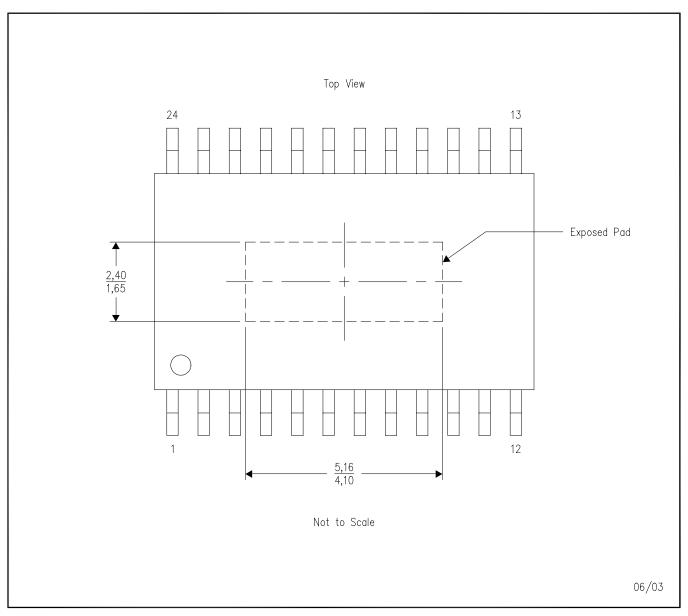


Figure 24. Typical Application, Monitor Supply

### PWP (R-PDSO-G24)

### **PowerPAD™ PLASTIC SMALL-OUTLINE**



NOTES:

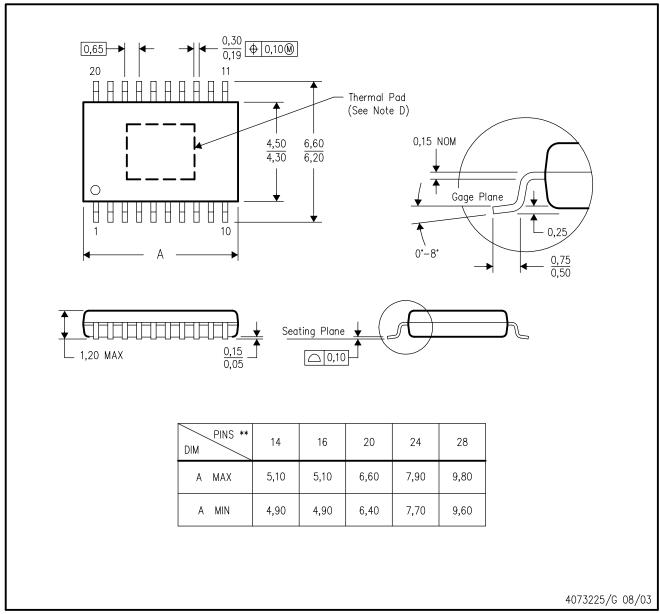
- A. All linear dimensions are in millimeters.
- This drawing is subject to change without notice.

  For additional information on the PowerPAD™ package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, *PowerPAD Thermally Enhanced Package*, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

# PWP (R-PDSO-G\*\*)

# PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE

20 PIN SHOWN



NOTES:

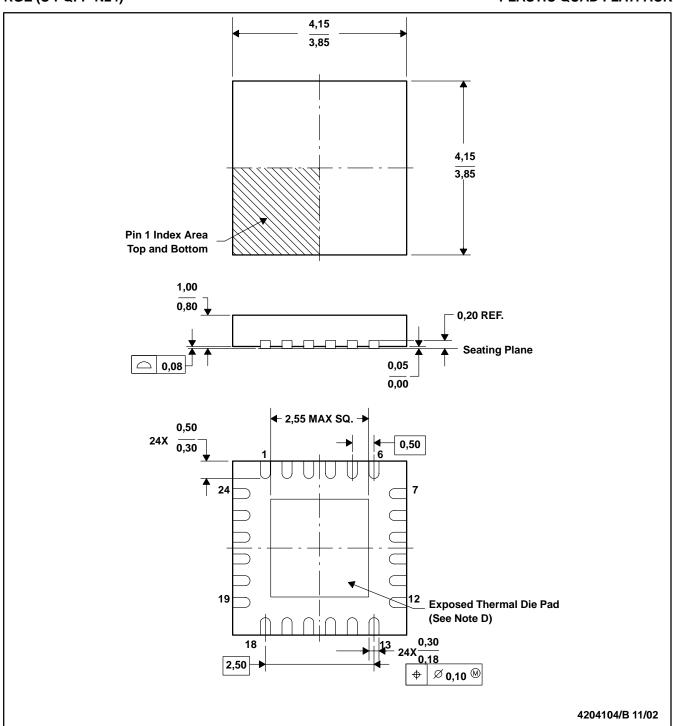
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusions.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="https://www.ti.com">www.ti.com</a>.
- E. Falls within JEDEC MO-153

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### RGE (S-PQFP-N24)

### PLASTIC QUAD FLATPACK



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Quad Flatpack, No-leads, (QFN) package configuration.
- D. The package thermal performance may be enhanced by bonding the thermal die pad to an external thermal plane.
- E. Falls within JEDEC M0-220.



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